

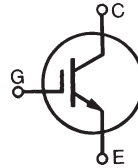
GenX3™ 1200V IGBTs

IXGA12N120A3
IXGP12N120A3
IXGH12N120A3

$V_{CES} = 1200V$
 $I_{C90} = 12A$
 $V_{CE(sat)} \leq 3.0V$

High Surge Current

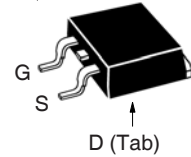
Ultra-Low V_{sat} PT IGBTs for up to 3kHz Switching



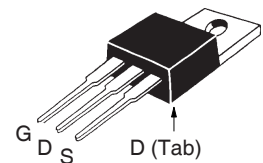
| Symbol | Test Conditions | Maximum Ratings | |
|-------------------------------|--|--|------------|
| V_{CES} | $T_J = 25^\circ C$ to $150^\circ C$ | 1200 | V |
| V_{CGR} | $T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$ | 1200 | V |
| V_{GES} | Continuous | ± 20 | V |
| V_{GEM} | Transient | ± 30 | V |
| I_{C25} | $T_C = 25^\circ C$ | 22 | A |
| I_{C90} | $T_C = 90^\circ C$ | 12 | A |
| I_{CM} | $T_C = 25^\circ C$, 1ms | 60 | A |
| SSOA (RBSOA) | $V_{GE} = 15V$, $T_{VJ} = 125^\circ C$, $R_G = 10\Omega$ Clamped Inductive Load | $I_{CM} = 24$ $V_{CE} \leq 0.8 \cdot V_{CES}$ | A |
| P_C | $T_C = 25^\circ C$ | 100 | W |
| T_J | | -55 ... +150 | $^\circ C$ |
| T_{JM} | | 150 | $^\circ C$ |
| T_{stg} | | -55 ... +150 | $^\circ C$ |
| T_L | Maximum Lead Temperature for Soldering | 300 | $^\circ C$ |
| T_{SOLD} | 1.6 mm (0.062in.) from Case for 10s | 260 | $^\circ C$ |
| F_C | Mounting Force (TO-263) | 10..65 / 2.2..14.6 | N/lb. |
| M_d | Mounting Torque (TO-220 & TO-247) | 1.13 / 10 | Nm/lb.in. |
| Weight | TO-263 | 2.5 | g |
| | TO-220 | 3.0 | g |
| | TO-247 | 6.0 | g |

| Symbol | Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified) | Characteristic Values | | |
|---------------|---|-----------------------|--------------|---------------------------|
| | | Min. | Typ. | Max. |
| BV_{CES} | $I_C = 250\mu A$, $V_{GE} = 0V$ | 1200 | | V |
| $V_{GE(th)}$ | $I_C = 250\mu A$, $V_{CE} = V_{GE}$ | 2.5 | | 5.0 V |
| I_{CES} | $V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 125^\circ C$ | | | 10 μA 275 μA |
| I_{GES} | $V_{CE} = 0V$, $V_{GE} = \pm 20V$ | | | ± 100 nA |
| $V_{CE(sat)}$ | $I_C = I_{C90}$, $V_{GE} = 15V$, Note 1 $T_J = 125^\circ C$ | | 2.40 2.75 | V V |

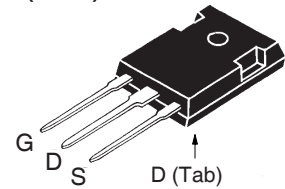
TO-263 AA (IXGA)



TO-220AB (IXGP)



TO-247 (IXGH)



G = Gate D = Drain
S = Source Tab = Drain

Features

- Optimized for Low Conduction Losses
- International Standard Packages

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts
- Inrush Current Protection Circuits

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

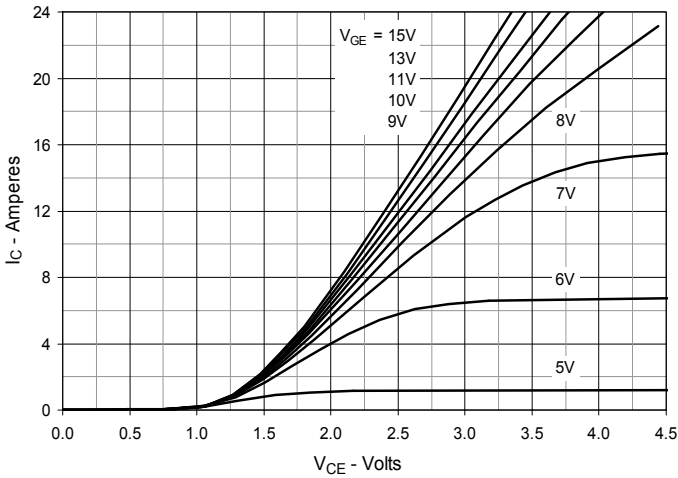


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

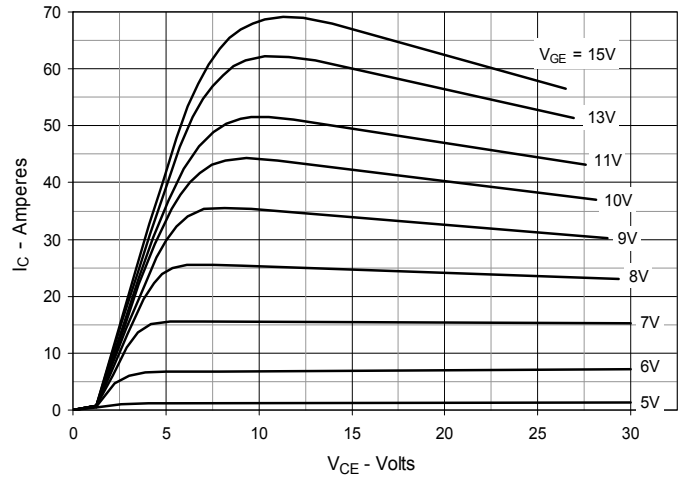


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

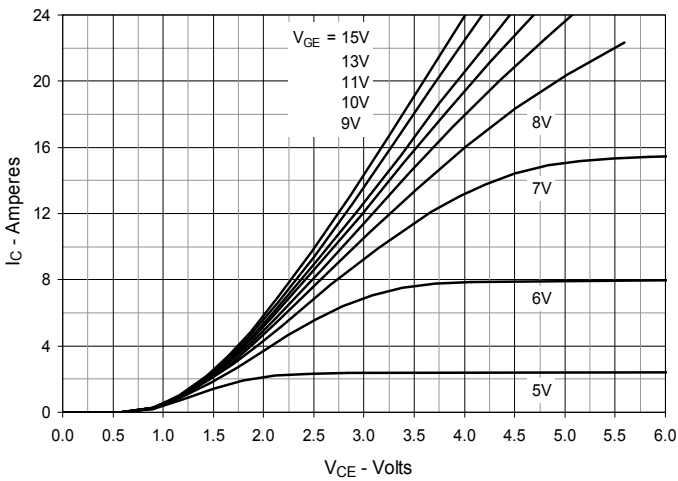


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

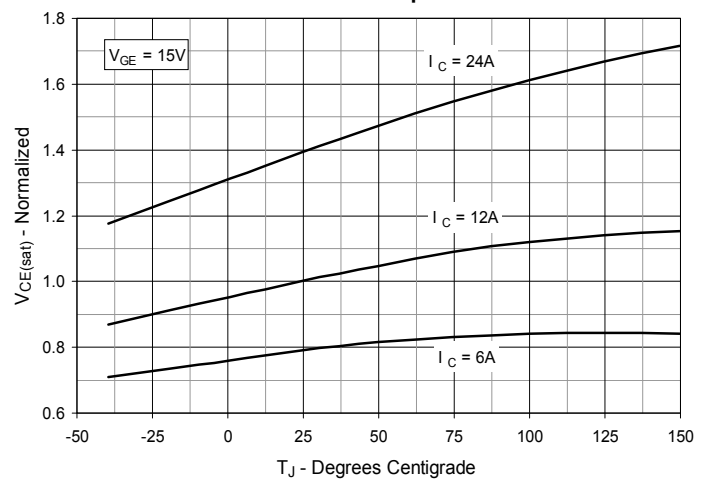


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

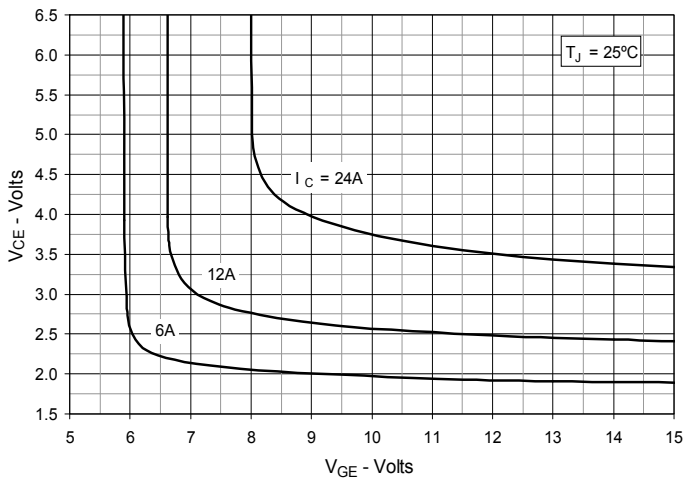


Fig. 6. Input Admittance

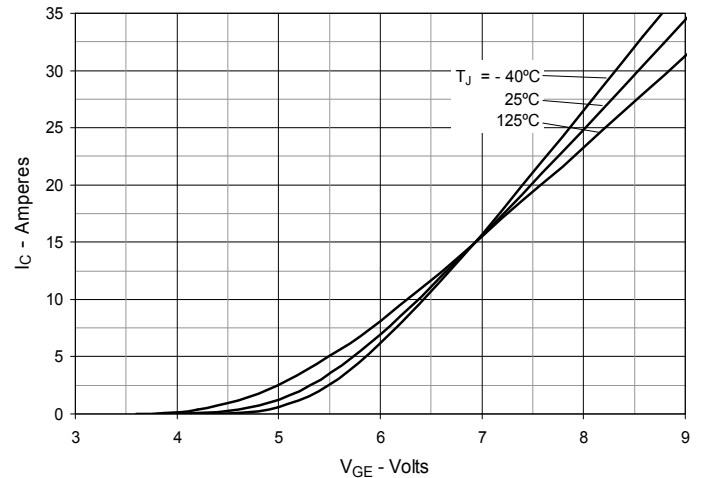


Fig. 7. Transconductance

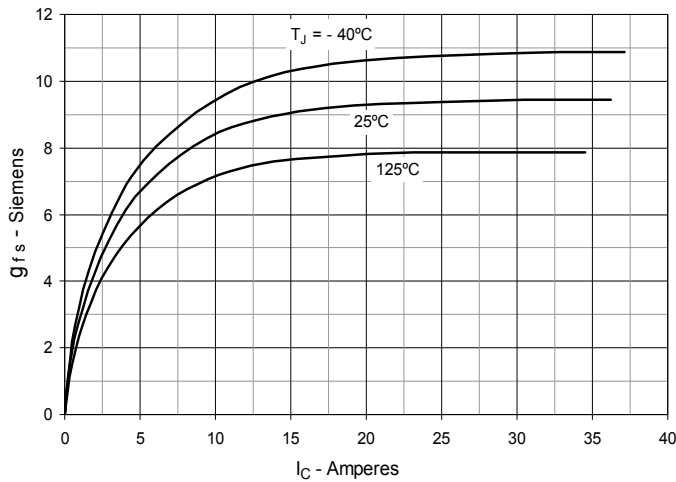


Fig. 8. Gate Charge

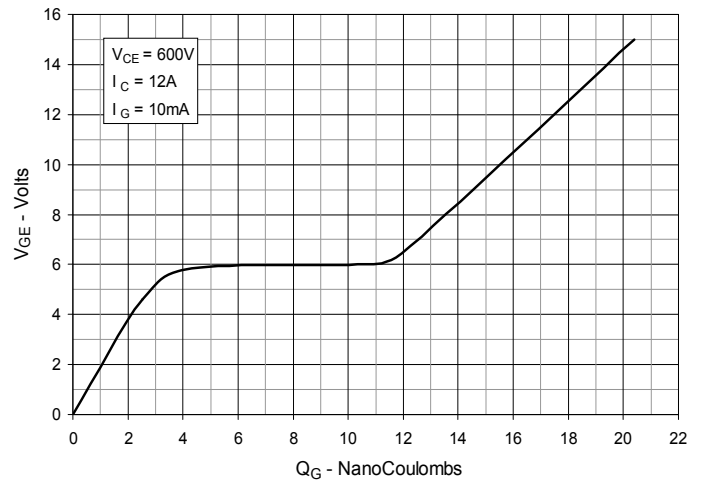


Fig. 9. Reverse-Bias Safe Operating Area

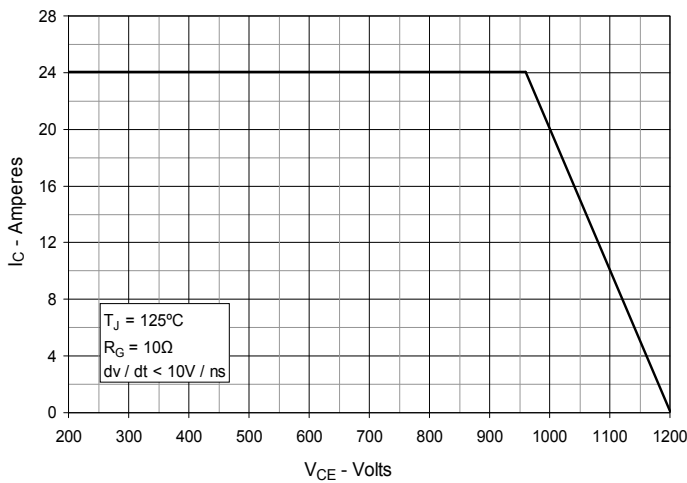


Fig. 10. Capacitance

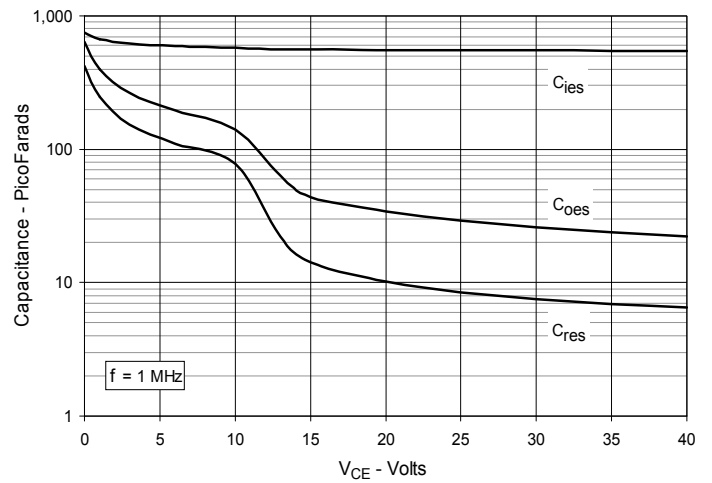


Fig. 11. Maximum Transient Thermal Impedance

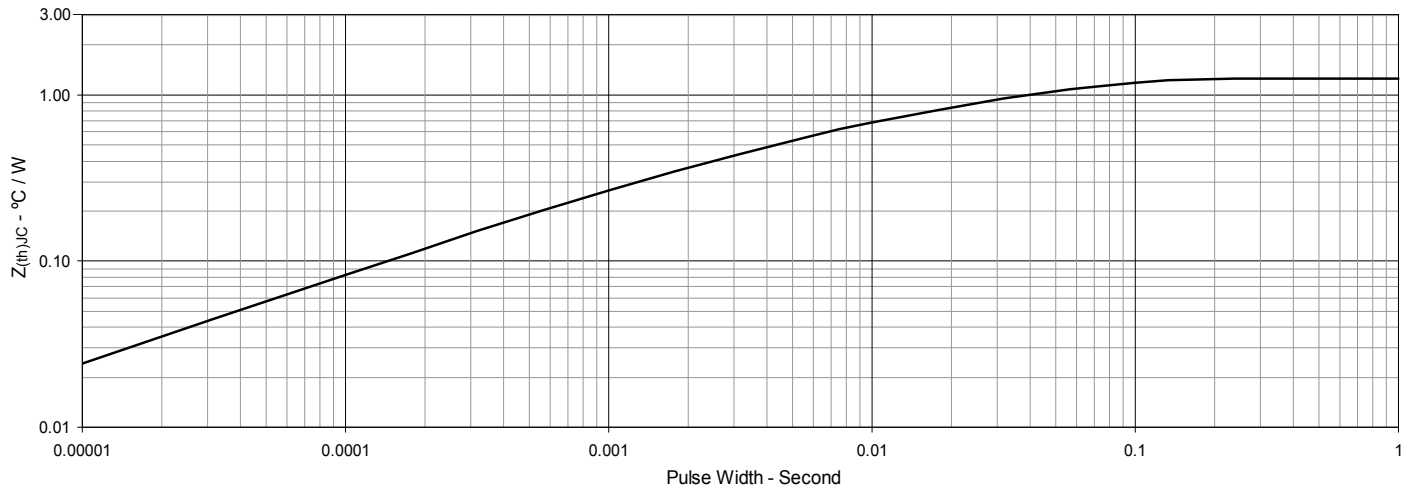


Fig. 12. Resistive Turn-on Rise Time vs. Junction Temperature

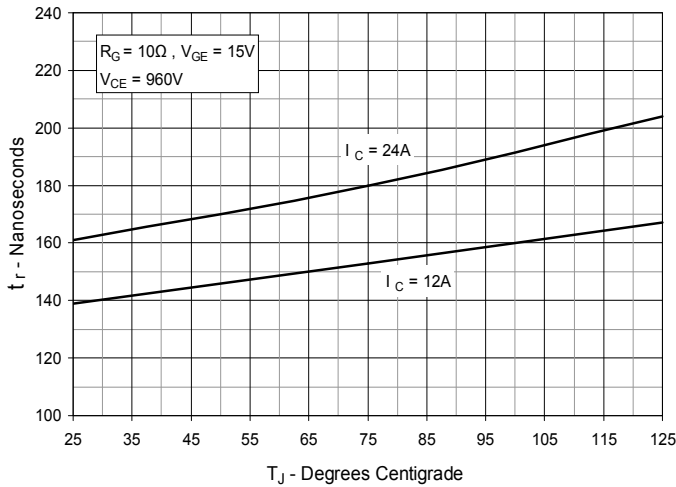


Fig. 13. Resistive Turn-on Rise Time vs. Collector Current

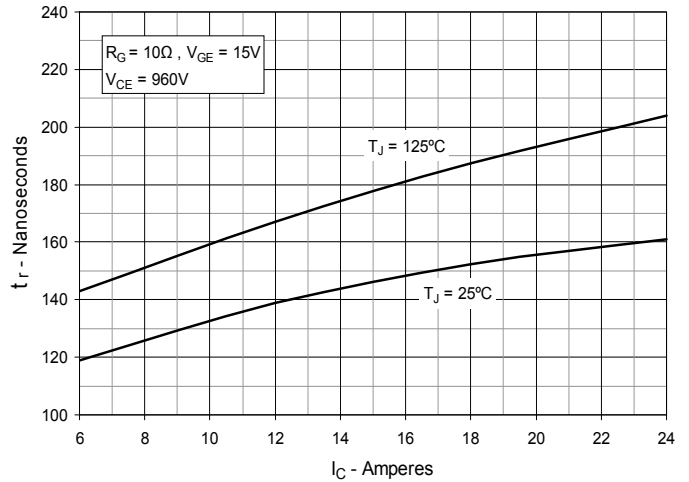


Fig. 14. Resistive Turn-on Switching Times vs. Gate Resistance

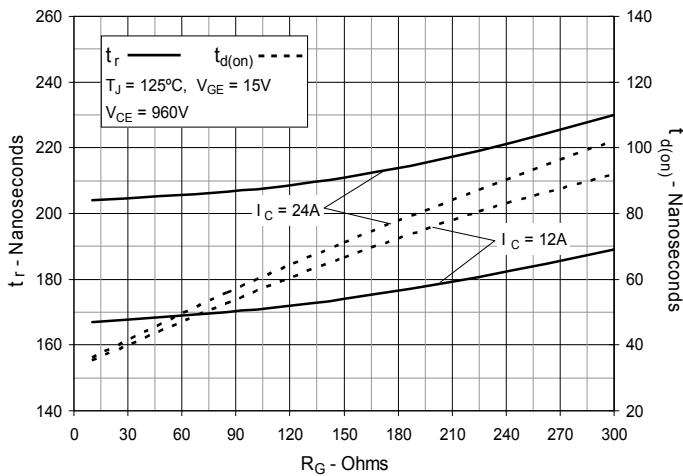


Fig. 15. Resistive Turn-off Switching Times vs. Junction Temperature

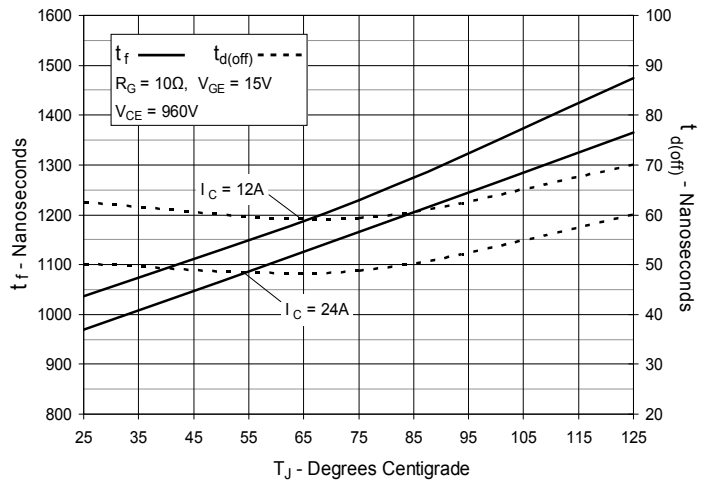


Fig. 16. Resistive Turn-off Switching Times vs. Collector Current

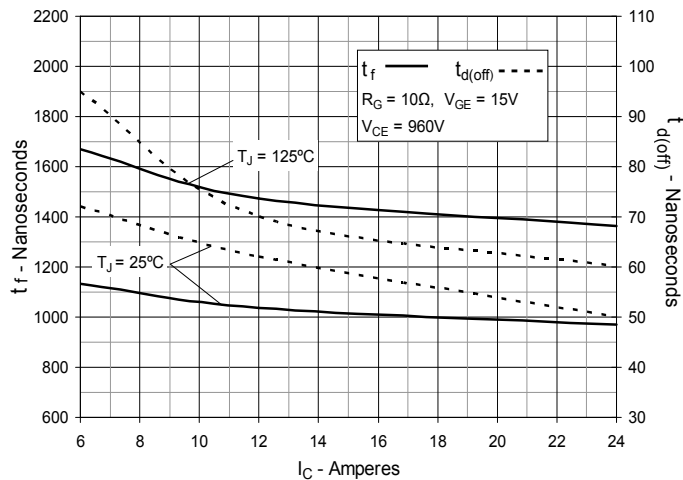
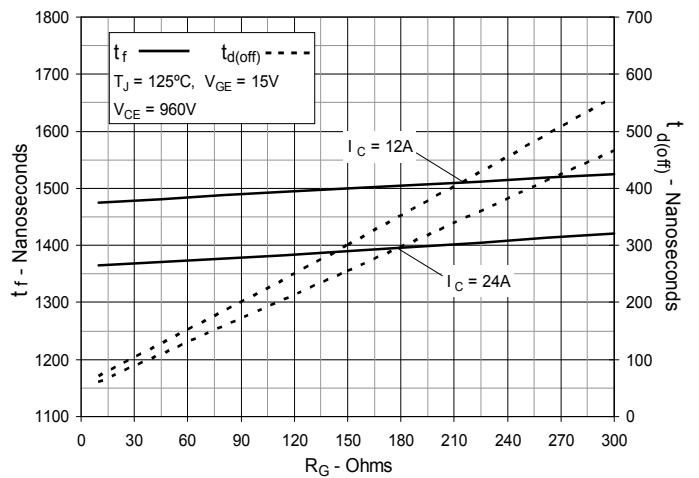


Fig. 17. Resistive Turn-off Switching Times vs. Gate Resistance



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